

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of manufacturing a semiconductor device, ~~the method comprising:~~

~~a peeling layer forming step of forming a peeling layer on a first substrate;~~

~~an insulating film forming step of forming an insulating film on the peeling layer;~~

~~a fine hole forming step of forming a plurality of fine holes in the insulating film;~~

~~a film forming step of forming a semiconductor film on the insulating film and in the fine holes;~~

~~a crystallization step of melting and crystallizing the semiconductor film by a heat treatment to form a crystalline semiconductor film including substantially single-crystalline grains substantially centered on the respective fine holes;~~

~~an element forming step of forming a semiconductor element by using the crystalline semiconductor film; and~~

~~a transfer step of causing peeling at the inside and/or the boundary surface of the peeling layer to separate the semiconductor element from the first substrate and transferring the semiconductor element to a second substrate.~~

2. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 1, ~~wherein the transfer step~~causing peeling comprises:

~~a bonding step of bonding the semiconductor element on the first substrate to the second substrate;~~

~~a peeling step of applying energy to the peeling layer to cause the peeling at the inside and/or the boundary surface of the peeling layer; and~~

~~a separation step of separating the first substrate from the second substrate.~~

3. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 1, ~~wherein the transfer step~~ causing peeling comprises:

~~a first bonding step of bonding the semiconductor element on the first substrate to a temporary transfer substrate;~~

~~a first peeling step of causing the peeling at the inside and/or the boundary surface of the peeling layer;~~

~~a first separation step of separating the first substrate from the temporary transfer substrate;~~

~~a second bonding step of bonding the semiconductor element on the temporary transfer substrate to the second substrate; and~~

~~a second separation step of separating the temporary transfer substrate from the second substrate.~~

4. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 2, ~~wherein the application of energy to the peeling layer is carried out by means of laser irradiation.~~

5. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 1, ~~wherein the first substrate has~~ having at least one of size, shape and thermal resistance suitable for a semiconductor process capable of processing at least a semiconductor wafer.

6. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 5, ~~wherein the semiconductor process is~~ being an LSI manufacturing process.

7. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 5, ~~wherein~~ the first substrate ~~has~~ having a wafer size.

8. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 1, ~~wherein~~ the surface roughness of the first substrate ~~ranges~~ ranging from 10 μm to 30 μm .

9. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 1, ~~wherein~~ in forming the semiconductor element ~~forming step~~, a plurality of the semiconductor elements ~~are~~ formed using one crystalline semiconductor film.

10. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 9, ~~wherein~~ the plurality of semiconductor elements constitute a unit circuit.

11. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 1, ~~wherein~~ in the ~~transfer step~~ causing peeling, only the semiconductor elements that are transfer targets among ~~the~~ a plurality of semiconductor elements formed on the first substrate ~~are~~ being selectively transferred from the first substrate to the second substrate.

12. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 11, ~~wherein~~ in the ~~transfer step~~ causing peeling, the semiconductor elements that are the transfer targets are selected correspondingly to a plurality of ~~the~~ crystalline semiconductor films, respectively.

13. (Currently Amended) The method of manufacturing a semiconductor device according to Claim 12, the method further ~~comprising~~ comprising:
_____ a division step of dividing the semiconductor elements and the peeling layer
formed on the first substrate every crystalline semiconductor film.

14. (Currently Amended) An electro-optical ~~device comprising device,~~
comprising:
_____the semiconductor device manufactured by using the method of manufacturing a
semiconductor device according to Claim 1.

15. (Currently Amended) An integrated ~~circuit comprising circuit, comprising:~~
_____the semiconductor device manufactured by using the method of manufacturing
a semiconductor device according to Claim 1.

16. (Currently Amended) A circuit ~~board comprising board, comprising:~~
_____the semiconductor device manufactured by using the method of manufacturing
a semiconductor device according to Claim 1.

17. (Currently Amended) An electronic ~~apparatus comprising apparatus,~~
comprising:
_____the semiconductor device manufactured by using the method of manufacturing
a semiconductor device according to Claim 1.